









# **CEU1610LA**

#### 100V Δ 13.4mΩ Δ 36A Δ Si MOSFET

SILICON Si MOSFET ▲ SMD type

N-channel enhancement mode

UL94V-0 rated flame retardant epoxy

TO252 (DPAK) package ▲ MSL 3

Super high dense cell density for extremely low R<sub>DS(ON)</sub>

High power and current handling capability

#### **MAXIMUM RATINGS**

Parameter (T <sub>C</sub> = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V <sub>DS</sub>	100V
Gate-Source Voltage	V <sub>GS</sub>	±20V
Continuous Drain Current at T <sub>C</sub> = 25°C	I <sub>D</sub>	36A
Continuous Drain Current at T <sub>C</sub> = 100°C	I <sub>D</sub>	22A
Pulsed Drain Current Note 1	I <sub>DM</sub> Note4	144A
Maximum Power Dissipation at T <sub>C</sub> = 25°C	P <sub>D</sub>	35.7W
Power Dissipation Derating above 25°C	$\Delta P_D$	0.28W/°C
Single Pulsed Avalanche Energy Note 5	E <sub>AS</sub>	10mJ
Single Pulsed Avalanche Current Note 5	I <sub>AS</sub>	4.5A
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

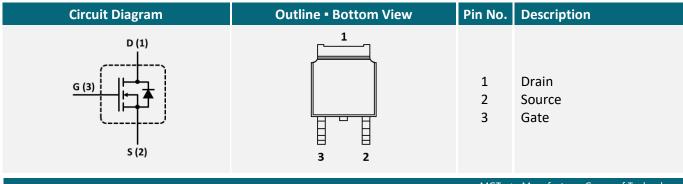
# THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R <sub>TH_JC</sub>	3.5°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R <sub>TH JA</sub>	50°C/W

# **APPLICATIONS**

Battery Management Systems	E-Bike	Industrial Control	Power Inverter	UPS
+4-	50			

### **PIN DESCRIPTION**





# **ELECTRICAL CHARACTERISTICS** ▲ T<sub>C</sub> = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_{D} = 250\mu A$	$BV_{DSS}$	100			V
Zero Gate Voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V$ , $V_{DS} = 0V$	$I_{GSSF}$			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	$I_{GSSR}$			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	$V_{GS(th)}$	1		2.5	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 20A$	R <sub>DS(ON)</sub>		13.4	16.5	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 4.5V$ , $I_D = 10A$	R <sub>DS(ON)</sub>		18	24	mΩ
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DS} = 50V, V_{GS} = 0V, f = 1MHz$	C <sub>ISS</sub>		900		pF
Output Capacitance	$V_{DS} = 50V$ , $V_{GS} = 0V$ , $f = 1MHz$	Coss		205		pF
Reverse Transfer Capacitance	$V_{DS} = 50V$ , $V_{GS} = 0V$ , $f = 1MHz$	$C_{RSS}$		15		pF
Switching Characteristics Note 3						
Turn-On Delay Time	$V_{DD} = 50V$ , $V_{GS} = 10V$ , $I_D = 1A$ , $R_{G(ext)} = 6\Omega$	t <sub>D(ON)</sub>		17		ns
Turn-On Rise Time	$V_{DD}$ = 50V, $V_{GS}$ = 10V, $I_D$ = 1A, $R_{G(ext)}$ = $6\Omega$	$t_{R}$		4		ns
Turn-Off Delay Time	$V_{DD}$ = 50V, $V_{GS}$ = 10V, $I_D$ = 1A, $R_{G(ext)}$ = $6\Omega$	t <sub>D(OFF)</sub>		42		ns
Turn-Off Fall Time	$V_{DD}$ = 50V, $V_{GS}$ = 10V, $I_D$ = 1A, $R_{G(ext)}$ = $6\Omega$	t <sub>F</sub>		20		ns
Total Gate Charge	$V_{DD} = 50V$ , $V_{GS} = 4.5V$ , $I_D = 20A$	$Q_{G}$		11.5		nC
Gate Source Charge	$V_{DD} = 50V$ , $V_{GS} = 4.5V$ , $I_D = 20A$	$Q_{GS}$		1.7		nC
Gate Drain Charge	$V_{DD} = 50V$ , $V_{GS} = 4.5V$ , $I_{D} = 20A$	$\mathbf{Q}_{GD}$		7.8		nC
<b>Drain-Source Diode Characteristics a</b>	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 2		Is			29	Α
Drain-Source Diode Forward Voltage Note 2	$V_{GS} = 0V$ , $I_S = 20A$	$V_{SD}$			1.2	V

#### Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3: Guaranteed by design, not subject to production testing.
- 4: Pulse width limited by safe operating area.
- 5: L = 0.1mH,  $I_{AS} = 4.5$ A,  $V_{DD} = 24$ V,  $R_G = 25$ Ω, Starting  $T_J = 25$ °C



#### REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



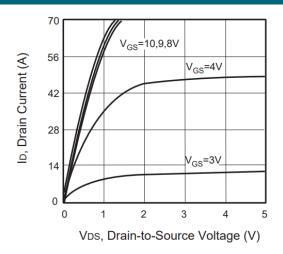


Fig. 2 • Transfer Characteristics

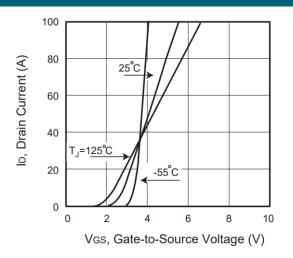


Fig. 3 • Capacitance

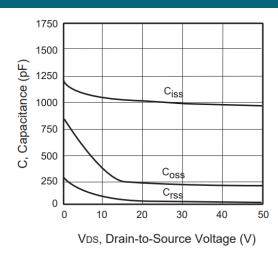


Fig. 4 • On-Resistance Variation with Temperature

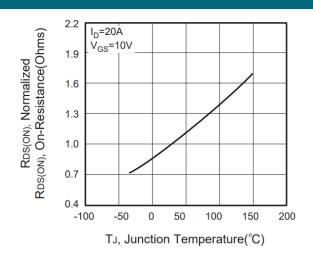


Fig. 5 • Gate Threshold Variation with Temperature

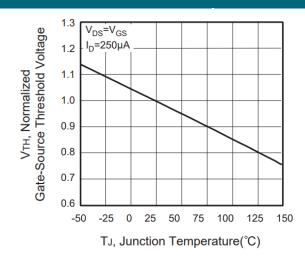
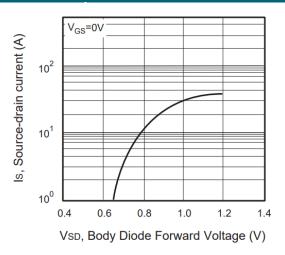


Fig. 6 • Body Diode Forward Voltage Variation with Source Current



MGT ▲ Manufacturer Group of Technology



#### REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 7 • Gate Charge

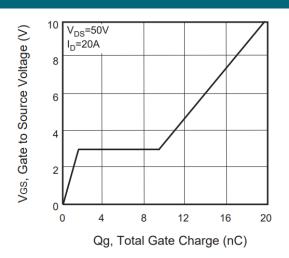


Fig. 8 • Maximum Safe Operating Area

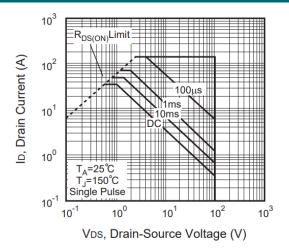


Fig. 9 • Breakdown Voltage Variation vs. Temperature

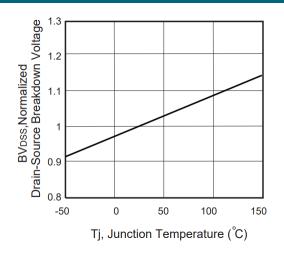
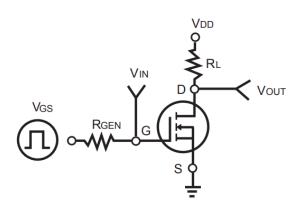
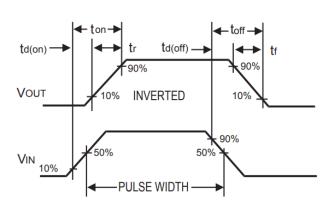


Fig. 10 • Switching Test Circuit

Fig. 11 • Switching Waveforms

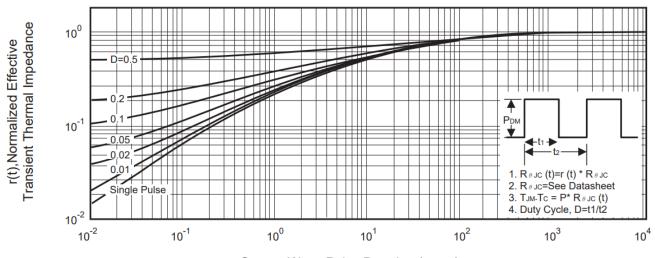






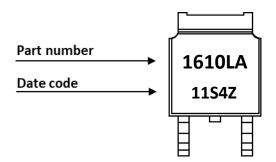
#### REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 12 • Normalized Thermal Transient Impedance Curve



Square Wave Pulse Duration (msec)

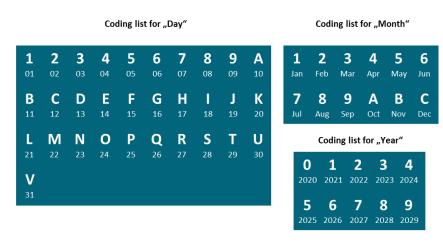
#### **PART MARKING**



#### **DATE CODE**

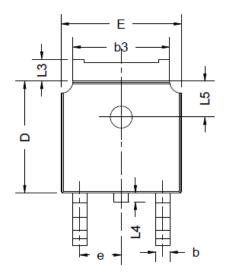
Example: 11S4Z

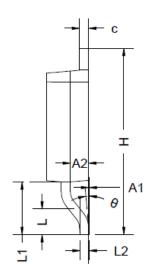


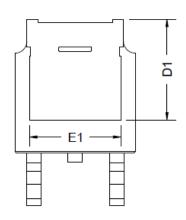


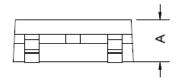


# **PACKAGE OUTLINE**









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)			
Α	2.20	2.30	2.38			
A1	0.00	-	0.20			
A2	A2 0.90		1.17			
b	b 0.68 0.78		0.90			
b3	5.23	5.33	5.46			
С	0.43 0.53		0.61			
D	D 5.98 6.10		6.22			
D1	5.30 REF					
Е	6.40 6.60		6.73			
E1	4.63	-	-			

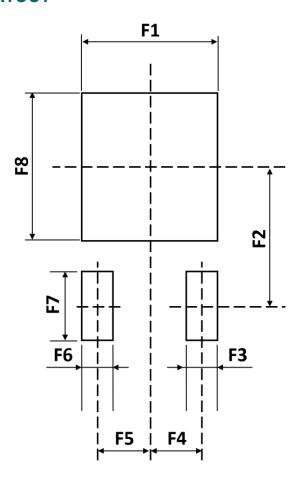
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)				
е		2.286 BSC					
Н	9.40	10.10	10.50				
L	1.38	1.50	1.75				
L1	2.90 REF						
L2		0.51 BSC					
L3	0.88	-	1.28				
L4	0.50		1.00				
L5	1.65	1.80	1.95				
θ	0°	-	8°				

# **ORDERING INFORMATION**

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEU1610LA	TO252 (DPAK)	Reel	2,500pcs	5,000pcs	40,000pcs



### **RECOMMENDED PAD LAYOUT**



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	6.00	-
F2	F2 - 6.25		-
F3	- 1.40		-
F4	-	2.29	-

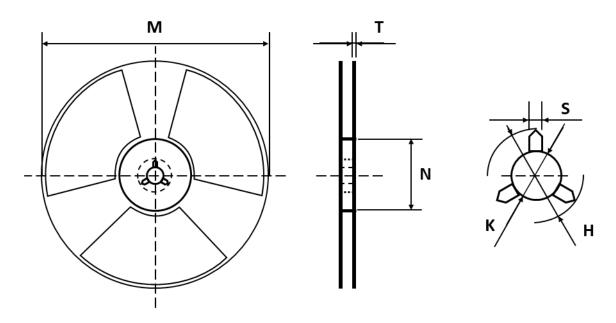
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F5	-	2.29	-
F6	-	1.40	-
F7	-	3.00	-
F8	-	6.50	-

#### **Notes:**

- 1. The suggested land pattern dimensions have been provided for reference only.
- 2. For further information, please reference document IPC-7351A.

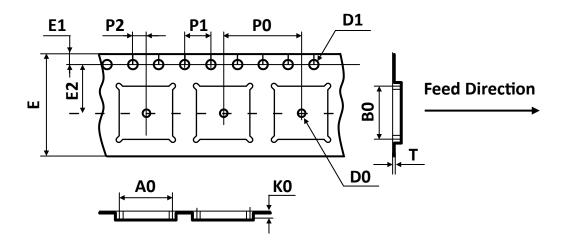


# **REEL DIMENSIONS** ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
16mm	Ø330	±2.00	±0.50	±0.20	+0 50	+0.50	+0.50
		±2.00	±0.50	±0.20	±0.50	-0.20	-0.20

# **TAPE DIMENSIONS** ▲ All dimensions in mm

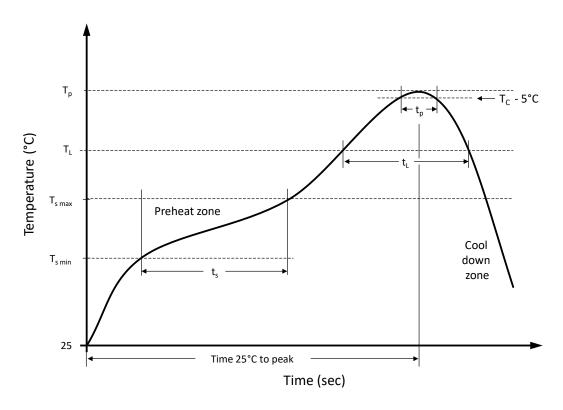


Package	A0	В0	КО	D0	D1	E	E1	E2	P0	P1	P2	Т
TO252	6.90	10.50	2.70	1.50	1.50	16.00	1.75	7.50	8.00	4.00	2.00	0.30
(DPAK)	±0.10	±0.10	±0.10	MIN	±0.10	+0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

Note: All dimensions meet EIA-481-D requirements.



# RECOMMENDED REFLOW SOLDERING PROFILE



# **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T <sub>s max</sub>	150 °C	200 °C
Preheat time t <sub>s</sub> from T <sub>s min</sub> to T <sub>s max</sub>	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	$T_L$	183 °C	217 °C
Time t <sub>L</sub> maintained above T <sub>L</sub>	t <sub>L</sub>	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t <sub>p</sub>	20 seconds max.	30 seconds max.
Ramp-down rate (T <sub>L</sub> to T <sub>p</sub> )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



#### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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